Preferred Devices

High Voltage Switching Diode

Device Marking:

- BAS19LT1 = JP
- BAS20LT1 = JR
- BAS21LT1 = JS
- BAS21DW5T1 = JS

Features

• Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage BAS19 BAS20 BAS21	V _R	120 200 250	Vdc
Repetitive Peak Reverse Voltage BAS19 BAS20 BAS21	V _{RRM}	120 200 250	Vdc
Continuous Forward Current	I _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	625	mAdc
Maximum Junction Temperature	T _{Jmax}	150	°C
Power Dissipation (Note 4)	P_{D}	385	mW

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

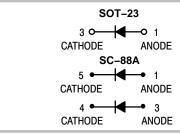
1. Mounted on FR-5 Board = 1.0 x 0.75 x 0.062 in.



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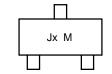
HIGH VOLTAGE SWITCHING DIODE



MARKING DIAGRAMS



SOT-23 (TO-236) **CASE 318** STYLE 8



Jx = Specific Device Code x = P. R or S

M = Date Code



SC-88A (SOT-353) **CASE 419A**



XX = Specific Device Code d = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS (SOT-23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 2)	P_{D}	225	mW
T _A = 25°C Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 3)	P _D	300	mW
T _A = 25°C Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

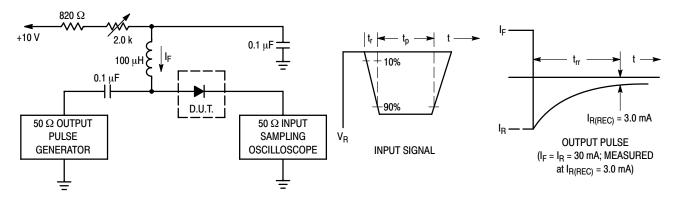
THERMAL CHARACTERISTICS (SC-88A)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P _D	385	mW
Thermal Resistance – Junction-to-Ambient Derate Above 25°C	$R_{ heta JA}$	328 3.0	°C/W mW/°C
Maximum Junction Temperature	T _{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 2. $FR-5 = 1.0 \times 0.75 \times 0.062$ in. 3. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina. 4. Mounted on FR-5 Board = $1.0 \times 0.75 \times 0.062$ in.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current	I _R			μAdc
$(V_R = 100 \text{ Vdc})$ BAS	19	_	0.1	
$(V_R = 150 \text{ Vdc})$ BAS	20	_	0.1	
$(V_R = 200 \text{ Vdc})$ BAS	21	_	0.1	
$(V_R = 100 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS	19	_	100	
$(V_R = 150 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS	20	_	100	
$(V_R = 200 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS	21	-	100	
Reverse Breakdown Voltage	V _(BR)			Vdc
$(I_{BR} = 100 \mu\text{Adc})$ BAS		120	-	
$(I_{BR} = 100 \mu\text{Adc})$ BAS	20	200	-	
$(I_{BR} = 100 \mu\text{Adc})$ BAS	21	250	_	
Forward Voltage	V _F			Vdc
$(I_F = 100 \text{ mAdc})$		_	1.0	
(I _F = 200 mAdc)		-	1.25	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30 \text{ mAdc}$, $I_{R(REC)} = 3.0 \text{ mAdc}$, $R_L = 10 \text{ mAdc}$)) t _{rr}	_	50	ns



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.

- 2. Input pulse is adjusted so I_{R(peak)} is equal to 30 mA.
- $3. t_p * t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

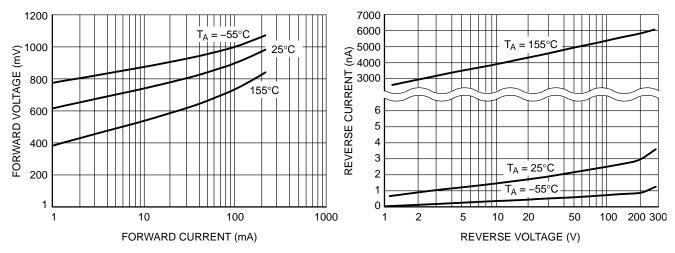


Figure 2. Forward Voltage

Figure 3. Reverse Leakage

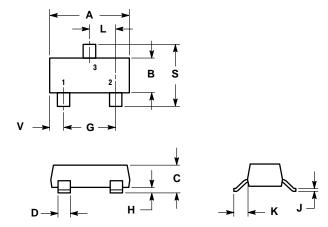
ORDERING INFORMATION

Device	Package	Shipping [†]	
BAS19LT1	SOT-23		
BAS19LT1G	SOT-23 (Pb-Free)	3000 Tape/Reel	
BAS19LT3	SOT-23		
BAS19LT3G	SOT-23 (Pb-Free)	10000 Tape/Reel	
BAS20LT1	SOT-23		
BAS20LT1G	SOT-23 (Pb-Free)	3000 Tape/Reel	
BAS21LT1	SOT-23		
BAS21LT1G	SOT-23 (Pb-Free)	3000 Tape/Reel	
BAS21LT3	SOT-23		
BAS21LT3G	SOT-23 (Pb-Free)	10000 Tape/Reel	
BAS21DW5T1	SC-88A		
BAS21DW5T1G	SC-88A (Pb-Free)	3000 Tape/Reel	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-09 **ISSUE AH**



NOTES:

- IOTES:
 1 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2 CONTROLLING DIMENSION: INCH.
 3 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS. IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. 318-01, -02, AND -06 OBSOLETE, NEW STANDARD 318-09.

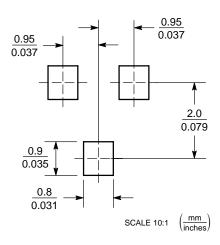
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN MAX	
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
Н	0.0040	0.0098	0.10	0.25
7	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
٧	0.0177	0.0236	0.45	0.60

STYLE 8: PIN 1. ANODE

NO CONNECTION

CATHODE

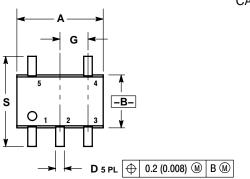
SOLDERING FOOTPRINT*

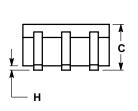


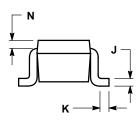
^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-88A (SOT-353) CASE 419A-02 ISSUE G





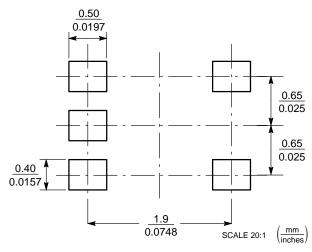


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
- 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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